Philippe VennÃ©guÃ¨s

List of Publications by Year
in descending order

207 papers	5,309 citations	76322 40 h-index	118840 62 g-index
211 all docs	211 docs citations	211 times ranked	3585 citing authors

#	Article	IF	Citations
1	Stress control in GaN grown on silicon (111) by metalorganic vapor phase epitaxy. Applied Physics Letters, 2001, 79, 3230-3232.	3.3	258
2	Physical characterization of molybdenum oxycarbide catalyst; TEM, XRD and XPS. Catalysis Today, 1995, 23, 251-267.	4.4	202
3	Reduction mechanisms for defect densities in GaN using one- or two-step epitaxial lateral overgrowth methods. Journal of Applied Physics, 2000, 87, 4175-4181.	2.5	177
4	Influence of in situ sapphire surface preparation and carrier gas on the growth mode of GaN in MOVPE. Journal of Crystal Growth, 1998, 187, 167-177.	1.5	122
5	Pyramidal defects in metalorganic vapor phase epitaxial Mg doped GaN. Applied Physics Letters, 2000, 77, 880-882.	3.3	114
6	Growth of high-quality GaN by low-pressure metal-organic vapour phase epitaxy (LP-MOVPE) from 3D islands and lateral overgrowth. Journal of Crystal Growth, 1999, 205, 245-252.	1.5	108
7	Defect characterization in ZnO layers grown by plasma-enhanced molecular-beam epitaxy on (0001) sapphire substrates. Applied Physics Letters, 2001, 79, 194-196.	3.3	107
8	Luminescence and reflectivity studies of undoped, n- and p-doped GaN on (0001) sapphire. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1997, 50, 97-104.	3.5	104
9	Optimisation of AlN and GaN growth by metalorganic vapour-phase epitaxy (MOVPE) on Si (111). Journal of Crystal Growth, 2000, 217, 13-25.	1.5	99
10	Cathodoluminescence spectroscopy of epitaxial-lateral-overgrown nonpolar (11-20) and semipolar (11-22) GaN in relation to microstructural characterization. Journal of Applied Physics, 2007, 101, 113101.	2.5	99
11	Growth of high quality crack-free AlGaN films on GaN templates using plastic relaxation through buried cracks. Journal of Applied Physics, 2003, 94, 6499-6507.	2.5	94
12	Polarity Control in Group-III Nitrides beyond Pragmatism. Physical Review Applied, 2016, 5, .	3.8	94
13	Molecular-beam epitaxy of gallium nitride on (0001) sapphire substrates using ammonia. Journal of Applied Physics, 1998, 83, 1379-1383.	2.5	84
14	Atomic structure of pyramidal defects in Mg-doped GaN. Physical Review B, 2003, 68, .	3.2	79
15	Microstructural Characterization of Semipolar GaN Templates and Epitaxial-Lateral-Overgrown Films Deposited onM-Plane Sapphire by Metalorganic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2007, 46, 4089-4095.	1.5	73
16	The effect of the Si/N treatment of a nitridated sapphire surface on the growth mode of GaN in low-pressure metalorganic vapor phase epitaxy. Applied Physics Letters, 1998, 73, 1278-1280.	3.3	71
17	Polarity inversion of GaN(0001) by a high Mg doping. Journal of Crystal Growth, 2004, 269, 249-256.	1.5	68
18	Defect reduction method in (11-22) semipolar GaN grown on patterned sapphire substrate by MOCVD: Toward heteroepitaxial semipolar GaN free of basal stacking faults. Journal of Crystal Growth, 2014, 404, 177-183.	1.5	61

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19	Microstructure of GaN epitaxial films at different stages of the growth process on sapphire (0 0 0 1). Journal of Crystal Growth, 1997, 173, 249-259.	1.5	60
20	Epitaxial relationships between GaN and Al2O3(0001) substrates. Applied Physics Letters, 1997, 70, 643-645.	3.3	59
21	Mg-enhanced lateral overgrowth of GaN on patterned GaN/sapphire substrate by selective Metal Organic Vapor Phase Epitaxy. MRS Internet Journal of Nitride Semiconductor Research, 1998, 3, 1.	1.0	59
22	Non-polar<i>a</i>-plane ZnMgO1/ZnO quantum wells grown by molecular beam epitaxy. Semiconductor Science and Technology, 2008, 23, 035005.	2.0	59
23	Interface structure and anisotropic strain relaxation of nonpolar wurtzite (112Â¯) and (101Â¯) orientations: ZnO epilayers grown on sapphire. Journal of Applied Physics, 2008, 104, .	2.5	57
24	Catalytic unzipping of carbon nanotubes to few-layer graphene sheets under microwaves irradiation. Applied Catalysis A: General, 2009, 371, 22-30.	4.3	57
25	Study of open-core dislocations in GaN films on (0001) sapphire. Applied Physics Letters, 1997, 70, 2434-2436.	3.3	56
26	Interfacial structure and defect analysis of nonpolar ZnO films grown on R-plane sapphire by molecular beam epitaxy. Journal of Applied Physics, 2008, 103, .	2.5	52
27	Indium incorporation dynamics into AlInN ternary alloys for laser structures lattice matched to GaN. Applied Physics Letters, 2008, 93, .	3.3	51
28	The critical role of growth temperature on the structural and electrical properties of AlGaN/GaN high electron mobility transistor heterostructures grown on Si(111). Journal of Applied Physics, 2009, 105, 033701.	2.5	50
29	Stacking faults blocking process in (11âˆ'22) semipolar GaN growth on sapphire using asymmetric lateral epitaxy. Journal of Crystal Growth, 2010, 312, 2625-2630.	1.5	48
30	Growth modes and microstructures of ZnO layers deposited by plasma-assisted molecular-beam epitaxy on (0001) sapphire. Journal of Applied Physics, 2001, 90, 5115-5119.	2.5	46
31	Dual-polarity GaN micropillars grown by metalorganic vapour phase epitaxy: Cross-correlation between structural and optical properties. Journal of Applied Physics, 2014, 115, .	2.5	45
32	Strain-compensated (Ga,In)N/(Al,Ga)N/GaN multiple quantum wells for improved yellow/amber light emission. Applied Physics Letters, 2015, 106, .	3.3	45
33	Structural changes in metastable epitaxial Co/Mn superlattices. Physical Review B, 1994, 49, 8561-8573.	3.2	44
34	GaN epitaxial growth on sapphire (0 0 0 1): the role of the substrate nitridation. Journal of Crystal Growth, 1997, 178, 220-228.	1.5	44
35	On the polarity of GaN micro- and nanowires epitaxially grown on sapphire (0001) and Si(111) substrates by metal organic vapor phase epitaxy and ammonia-molecular beam epitaxy. Applied Physics Letters, 2011, 98, 011914.	3.3	44
36	A Two-Step Method for Epitaxial Lateral Overgrowth of GaN. Physica Status Solidi A, 1999, 176, 567-571.	1.7	42

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37	Reduction of stacking faults in (11$ ar 2 $0) and (11$ ar 2 $2) GaN films by ELO techniques and benefit on GaN wells emission. Physica Status Solidi (A) Applications and Materials Science, 2007, 204, 282-289.	1.8	42
38	Transmission electron microscopy study of the nitridation of the (0001) sapphire surface. Applied Physics Letters, 1999, 75, 4115-4117.	3.3	41
39	Growth of non-polar ZnO/(Zn,Mg)O quantum well structures on R-sapphire by plasma-assisted molecular beam epitaxy. Journal of Crystal Growth, 2007, 301-302, 366-369.	1.5	41
40	Defect reduction methods for III-nitride heteroepitaxial films grown along nonpolar and semipolar orientations. Semiconductor Science and Technology, 2012, 27, 024004.	2.0	41
41	GaInN/GaN multiple-quantum-well light-emitting diodes grown by molecular beam epitaxy. Applied Physics Letters, 1999, 74, 3616-3618.	3.3	40
42	Crack-Free Thick GaN Layers on Silicon (111) by Metalorganic Vapor Phase Epitaxy. Physica Status Solidi A, 2001, 188, 531-535.	1.7	40
43	Use of thulium-doped LaF3 nanoparticles to lower the phonon energy of the thulium's environment in silica-based optical fibres. Optical Materials, 2017, 68, 24-28.	3.6	39
44	Control of the polarity of GaN films using an Mg adsorption layer. Journal of Crystal Growth, 2003, 251, 460-464.	1.5	38
45	Epitaxial lateral overgrowth of GaN on Si (111). Journal of Applied Physics, 2003, 93, 182-185.	2.5	38
46	Study of the epitaxial relationships between III-nitrides and M-plane sapphire. Journal of Applied Physics, 2010, 108, 113521.	2.5	38
47	Fiberâ€drawâ€induced elongation and breakâ€up of particles inside the core of a silicaâ€based optical fiber. Journal of the American Ceramic Society, 2017, 100, 1814-1819.	3.8	38
48	Strong decrease of the activation energy as a function of A1 content in FeAlx alloys (x â‰¦ 30 at.%) deduced from kinetic measurements of ordering. Acta Metallurgica Et Materialia, 1990, 38, 2199-2213.	1.8	37
49	Structural and optical properties of lattice-matched ZnBeSe layers grown by molecular-beam epitaxy onto GaAs substrates. Applied Physics Letters, 1997, 70, 3564-3566.	3.3	37
50	Anisotropic morphology of nonpolar a-plane GaN quantum dots and quantum wells. Journal of Applied Physics, 2007, 102, 074304.	2.5	37
51	Dislocation densities reduction in MBE-grown AlN thin films by high-temperature annealing. Journal of Crystal Growth, 2017, 461, 10-15.	1.5	37
52	Intentional polarity conversion of AlN epitaxial layers by oxygen. Scientific Reports, 2018, 8, 14111.	3.3	36
53	Influence of high Mg doping on the microstructural and optoelectronic properties of GaN. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 93, 224-228.	3.5	35
54	Relaxation mechanisms in metal-organic vapor phase epitaxy grown Al-rich (Al,Ga)Nâˆ•GaN heterostructures. Journal of Applied Physics, 2005, 97, 024912.	2.5	34

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55	Evidence of multimicrometric coherent Î³â€² precipitates in a hotâ€forged Î³â€“Î³â€² nickelâ€based superalloy. Journal of Microscopy, 2016, 263, 106-112.	1.8	34
56	Structural and electronic properties of ZnMgO/ZnO quantum wells. Superlattices and Microstructures, 2005, 38, 455-463.	3.1	33
57	Submicron periodic poling and chemical patterning of GaN. Applied Physics Letters, 2005, 87, 062106.	3.3	33
58	Evolution and prevention of meltback etching: Case study of semipolar GaN growth on patterned silicon substrates. Journal of Applied Physics, 2017, 122, .	2.5	33
59	Epitaxial orientation of III-nitrides grown on R-plane sapphire by metal-organic-vapor-phase epitaxy. Applied Physics Letters, 2006, 89, 111915.	3.3	32
60	Band-edge photoluminescence and reflectivity of nonpolar<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mo>(</mml:mo><mml:mn>11</mml:mn><mml:mover) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 547 T semipolar<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow	3.2	32
61	Imaging and counting threading dislocations in c-oriented epitaxial GaN layers. Semiconductor Science and Technology, 2013, 28, 035006.	2.0	32
62	In situimaging of threading dislocation terminations at the surface of GaN(0001) epitaxially grown on Si(111). Physical Review B, 2000, 61, 7618-7621.	3.2	31
63	Polar and semipolar GaN/Al_{0.5}Ga_{0.5}N nanostructures for UV light emitters. Semiconductor Science and Technology, 2014, 29, 084001.	2.0	30
64	Dislocation filtering and polarity in the selective area growth of GaN nanowires by continuous-flow metal organic vapor phase epitaxy. Applied Physics Express, 2016, 9, 015502.	2.4	30
65	Growth of Co/Ru strained superlattices. Journal of Magnetism and Magnetic Materials, 1992, 104-107, 1873-1875.	2.3	29
66	Structural Defects and Relation with Optoelectronic Properties in Highly Mg-Doped GaN. Physica Status Solidi A, 2002, 192, 394-400.	1.7	29
67	Growth and characterization of A-plane ZnO and ZnCoO based heterostructures. Applied Physics A: Materials Science and Processing, 2007, 88, 65-69.	2.3	28
68	Effects of capping on GaN quantum dots deposited on Al0.5Ga0.5N by molecular beam epitaxy. Applied Physics Letters, 2009, 94, 143105.	3.3	28
69	Impact of sapphire nitridation on formation of Al-polar inversion domains in N-polar AlN epitaxial layers. Journal of Applied Physics, 2017, 122, .	2.5	28
70	Characterization of High-k Ta[sub 2]Si Oxidized Films on 4H-SiC and Si Substrates as Gate Insulator. Journal of the Electrochemical Society, 2005, 152, G259.	2.9	27
71	Characterization of structural defects in (110) GaN films grown on (102) sapphire substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1658-1661.	0.8	27
72	Optimization of Si/N Treatment Time of Sapphire Surface and Its Effect on the MOVPE GaN Overlayers. Physica Status Solidi A, 1999, 176, 677-681.	1.7	26

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73	Phase separation in metalorganic vapor-phase epitaxy AlxGa(1â^'x)N films deposited on 6Hâ€"SiC. Applied Physics Letters, 2000, 77, 4310-4312.	3.3	26
74	High-quality distributed Bragg reflectors based on AlxGa1â^'xN/GaN multilayers grown by molecular-beam epitaxy. Applied Physics Letters, 2001, 79, 2136-2138.	3.3	25
75	Transmission electron microscopy investigation of microtwins and double positioning domains in (111) 3C-SiC in relation with the carbonization conditions. Applied Physics Letters, 2009, 95, .	3.3	25
76	On the origin of basal stacking faults in nonpolar wurtzite films epitaxially grown on sapphire substrates. Journal of Applied Physics, 2012, 112, .	2.5	25
77	Comparative study of GaN layers grown on insulating AlN and conductive AlGaN buffer layers. Semiconductor Science and Technology, 1999, 14, L33-L36.	2.0	24
78	Correlation between threading dislocation density and the refractive index of AlN grown by molecular-beam epitaxy on Si(111). Applied Physics Letters, 2003, 82, 1386-1388.	3.3	24
79	Growth of semipolar (202Ì„1) GaN layers on patterned silicon (114) 1Â° off by Metal Organic Vapor Phase Epitaxy. Journal of Crystal Growth, 2015, 419, 88-93.	1.5	24
80	In situgrowth monitoring of distributed GaNâ€"AlGaN Bragg reflectors by metalorganic vapor phase epitaxy. Applied Physics Letters, 2002, 80, 174-176.	3.3	23
81	AlGaN/GaN/AlGaN DH-HEMTs grown by MBE on Si(111). Journal of Crystal Growth, 2005, 278, 393-396.	1.5	23
82	Strain engineering in GaN layers grown on silicon by molecular beam epitaxy: The critical role of growth temperature. Journal of Crystal Growth, 2009, 311, 2002-2005.	1.5	23
83	GaN/Al0.5Ga0.5N (11-22) semipolar nanostructures: A way to get high luminescence efficiency in the near ultraviolet range. Journal of Applied Physics, 2011, 110, .	2.5	23
84	Substrate free GaAs photovoltaic cells on Pd-coated silicon with a 20% AM1.5 efficiency. IEEE Transactions on Electron Devices, 1996, 43, 1806-1811.	3.0	22
85	Electron energy-loss spectroscopy characterization of pyramidal defects in metalorganic vapor-phase epitaxy Mg-doped GaN thin films. Applied Physics Letters, 2000, 77, 2115-2117.	3.3	22
86	Hexagonal c-axis GaN layers grown by metalorganic vapor-phase epitaxy on Si(001). Journal of Crystal Growth, 2005, 280, 44-53.	1.5	21
87	Ductile relaxation in cracked metal-organic chemical-vapor-deposition-grown AlGaN films on GaN. Journal of Applied Physics, 2005, 97, 123504.	2.5	21
88	Three-dimensionally nucleated growth of gallium nitride by low-pressure metalorganic vapour phase epitaxy. Journal of Crystal Growth, 2003, 258, 232-250.	1.5	20
89	Proposition of a model elucidating the AlN-on-Si (111) microstructure. Journal of Applied Physics, 2018, 123, .	2.5	20
90	On the morphologies of oxides particles in optical fibers: Effect of the drawing tension and composition. Optical Materials, 2019, 87, 74-79.	3.6	20

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91	Nature and origin of V-defects present in metalorganic vapor phase epitaxy-grown (InxAl1â ˆ'x)N layers as a function of InN content, layer thickness and growth parameters. Journal of Crystal Growth, 2012, 353, 108-114.	1.5	19
92	Study of defect management in the growth of semipolar (11-22) GaN on patterned sapphire. Journal Physics D: Applied Physics, 2015, 48, 325103.	2.8	18
93	Lattice relaxation and threeâ€dimensional reflection highâ€energy electronâ€diffraction analysis of strained epitaxial Co/Mn superlattices. Journal of Applied Physics, 1994, 76, 2817-2824.	2.5	17
94	Internal quantum efficiencies of AlGaN quantum dots grown by molecular beam epitaxy and emitting in the UVA to UVC ranges. Journal of Applied Physics, 2019, 126, .	2.5	17
95	MBE-grown high-quality (Al,Ga)N/GaN distributed Bragg reflectors for resonant cavity LEDs. Semiconductor Science and Technology, 2001, 16, 913-917.	2.0	16
96	AlGaN-Based Light Emitting Diodes Using Self-Assembled GaN Quantum Dots for Ultraviolet Emission. Japanese Journal of Applied Physics, 2013, 52, 08JG01.	1.5	16
97	Heteroepitaxial growth of BeSe on vicinal Si(001) surfaces. Applied Physics Letters, 1998, 73, 957-959.	3.3	15
98	AlGaN/GaN HEMTs grown on silicon (001) substrates by molecular beam epitaxy. Superlattices and Microstructures, 2006, 40, 295-299.	3.1	15
99	Phase separation in GaN/AlGaN quantum dots. Applied Physics Letters, 2009, 95, 141901.	3.3	14
100	Metal Organic Vapor Phase Epitaxy of Monolithic Two-Color Light-Emitting Diodes Using an InGaN-Based Light Converter. Applied Physics Express, 2013, 6, 092105.	2.4	14
101	Blue Light-Emitting Diodes Grown on ZnO Substrates. Applied Physics Express, 2013, 6, 042101.	2.4	14
102	Influence of the heterostructure design on the optical properties of GaN and Al0.1Ga0.9N quantum dots for ultraviolet emission. Journal of Applied Physics, 2017, 122, .	2.5	14
103	The ternary system holmium-boron-carbon; isothermal section at 1500 Â°C. Journal of the Less Common Metals, 1985, 110, 295-298.	0.8	13
104	Correlation between the structural and transport properties of granular CoAg systems prepared by MBE. Journal of Magnetism and Magnetic Materials, 1995, 148, 313-314.	2.3	13
105	Epitaxial Lateral Overgrowth of GaN on Silicon (111). Physica Status Solidi A, 2001, 188, 733-737.	1.7	13
106	Growth of wurtzite-GaN on silicon (100) substrate by molecular beam epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 2187-2190.	0.8	13
107	Influence of 3Câ€"SiC/Si (111) template properties on the strain relaxation in thick GaN films. Journal of Crystal Growth, 2014, 398, 23-32.	1.5	13
108	Direct insight into grains formation in Si layers grown on 3C-SiC by chemical vapor deposition. Acta Materialia, 2015, 98, 336-342.	7.9	13

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109	Investigation of Al_yGa_{1âˆ’} _yN/Al_{0.5}Ga_{0.5}N quantum dot properties for the design of ultraviolet emitters. Japanese Journal of Applied Physics, 2016, 55, 05FG06.	1.5	13
110	Defect blocking via laterally induced growth of semipolar (1â€‰0â€‰1Ì…â€‰1) GaN on patterned substrates. Journal Physics D: Applied Physics, 2016, 49, 475104.	2.8	13
111	Î³â€² precipitates with a twin orientation relationship to their hosting grain in a Î³-Î³â€² nickel-based superalloy. Scripta Materialia, 2018, 153, 10-13.	5.2	13
112	Demonstration of Electrically Injected Semipolar Laser Diodes Grown on Low-Cost and Scalable Sapphire Substrates. ACS Applied Materials & Interfaces, 2019, 11, 47106-47111.	8.0	13
113	Filtering of Defects in Semipolar (11âˆ’22) GaN Using 2-Steps Lateral Epitaxial Overgrowth. Nanoscale Research Letters, 2010, 5, 1878-1881.	5.7	12
114	Successive selective growth of semipolar (11-22) GaN on patterned sapphire substrate. Semiconductor Science and Technology, 2015, 30, 065001.	2.0	12
115	Correlative investigation of Mg doping in GaN layers grown at different temperatures by atom probe tomography and off-axis electron holography. Nanotechnology, 2020, 31, 045702.	2.6	12
116	Molecular beam epitaxy of quantum well structures. Journal of Crystal Growth, 1996, 160, 211-219.	1.5	11
117	In-Plane Polarities of Nonpolar Wurtzite Epitaxial Films Deposited on<i>m</i>- and<i>r</i>-plane Sapphire Substrates. Japanese Journal of Applied Physics, 2009, 48, 090211.	1.5	11
118	Anisotropic chemical etching of semipolar {10ar {1}ar {1}}mbox {/} {10ar {1}{+}1} ZnO crystallographic planes: polarity versus dangling bonds. Nanotechnology, 2009, 20, 065701.	2.6	11
119	Study of the growth mechanisms of GaN/(Al, Ga)N quantum dots: Correlation between structural and optical properties. Journal of Applied Physics, 2011, 109, 053514.	2.5	11
120	AlGaN/GaN HEMTs with an InGaN backâ€barrier grown by ammoniaâ€assisted molecular beam epitaxy. Physica Status Solidi (A) Applications and Materials Science, 2013, 210, 480-483.	1.8	11
121	Semipolar (10-11) GaN growth on silicon-on-insulator substrates: Defect reduction and meltback etching suppression. Journal of Applied Physics, 2019, 125, .	2.5	11
122	Investigation of AlN films grown by molecular beam epitaxy on vicinal Si(111) as templates for GaN quantum dots. Applied Physics Letters, 2006, 89, 231903.	3.3	10
123	Growth optimization and characterization of lattice-matched Al0.82In0.18N optical confinement layer for edge emitting nitride laser diodes. Journal of Crystal Growth, 2012, 338, 20-29.	1.5	10
124	Growth of Ga- and N-polar GaN layers on O face ZnO substrates by molecular beam epitaxy. Journal of Crystal Growth, 2014, 388, 35-41.	1.5	10
125	Properties of AlN layers grown on c-sapphire substrate using ammonia assisted MBE. Journal of Crystal Growth, 2018, 499, 40-46.	1.5	10
126	Ferromagnetic resonance determination of fccâ†’hcp structural change in epitaxial Co/Mn superlattices. Journal of Applied Physics, 1994, 75, 5601-5603.	2.5	9

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127	Effect of the nucleation layer deposition temperature on the nature of defects in GSMBE GaN films. Journal of Crystal Growth, 1999, 201-202, 423-428.	1.5	9
128	Study of (Al,Ga)N Bragg Mirrors Grown on Al2O3(0001) and Si(111) by Metalorganic Vapor Phase Epitaxy. Physica Status Solidi A, 2001, 188, 899-903.	1.7	9
129	Plasmon energy from strained GaN quantum wells. Applied Physics Letters, 2013, 103, 021901.	3.3	9
130	Capping green emitting (Ga,In)N quantum wells with (Al,Ga)N: impact on structural and optical properties. Semiconductor Science and Technology, 2014, 29, 035016.	2.0	9
131	Selective heteroepitaxy on deeply grooved substrate: A route to low cost semipolar GaN platforms of bulk quality. Applied Physics Letters, 2016, 109, 082101.	3.3	8
132	Microstructural studies of GaN grown on (0001) sapphire by MOVPE. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1997, 43, 274-278.	3.5	7
133	Strain- and surface-induced modification of photoluminescence from self-assembled GaN/Al_{0.5}Ga_{0.5}N quantum dots: strong effect of capping layer and atmospheric condition. Nanotechnology, 2014, 25, 305703.	2.6	7
134	UVA and UVB light emitting diodes with Al_{<i>y</i>}Ga_{1âˆ’<i>y</i>}N quantum dot active regions covering the 305â€“335 nm range. Semiconductor Science and Technology, 2018, 33, 075007.	2.0	7
135	Investigations by high-resolution X-ray diffraction (HRXRD) and transmission electron microscopy (TEM) of (BeTe/ZnSe) superlattices grown by molecular beam epitaxy onto GaAs buffer epilayer. Journal of Crystal Growth, 1999, 201-202, 498-501.	1.5	6
136	Molecular-beam epitaxy of ZnxBe1âˆ’xSe layers on vicinal Si(001) substrates. Journal of Crystal Growth, 1999, 201-202, 514-517.	1.5	6
137	Molecular beam epitaxy of ZnxBe1âˆ’xSe: Influence of the substrate nature and epilayer properties. Journal of Electronic Materials, 2000, 29, 883-886.	2.2	6
138	Ta[sub 2]Si Thermal Oxidation: A Simple Route to a High-k Gate Dielectric on 4H-SiC. Electrochemical and Solid-State Letters, 2004, 7, F93.	2.2	6
139	Fabrication and growth of GaN-based micro and nanostructures. International Journal of Nanotechnology, 2012, 9, 412.	0.2	6
140	Green emission from semipolar InGaN quantum wells grown on lowâ€defect () GaN templates fabricated on patterned <i>r</i>â€sapphire. Physica Status Solidi (B): Basic Research, 2016, 253, 105-111.	1.5	6
141	Optimized In composition and quantum well thickness for yellow-emitting (Ga,In)N/GaN multiple quantum wells. Journal of Crystal Growth, 2016, 434, 25-29.	1.5	6
142	GaN films and GaN/AlGaN quantum wells grown by plasma assisted molecular beam epitaxy using a high density radical source. Journal of Crystal Growth, 2016, 433, 165-171.	1.5	6
143	Reduced nonradiative recombination in semipolar green-emitting III-N quantum wells with strain-reducing AlInN buffer layers. Applied Physics Letters, 2019, 115, 202103.	3.3	6
144	Microstructure of epitaxial Mg3N2 thin films grown by MBE. Journal of Applied Physics, 2021, 129, 095303.	2.5	6

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145	Crystalline magnesium nitride (<mml:math) Tj ETQq1 1 0.784314 rgBT /Overlock 10 Tf 50 762 Td (xmlns:mml="http://www.w3.org/199 From epitaxial growth to fundamental physical properties. Physical Review Materials, 2020, 4, .	2.4	6
146	Plan-view microstructures of Co/Ru bilayers. Journal of Materials Research, 1995, 10, 1539-1545.	2.6	5
147	Microstructural study of pseudomorphic ZnSe films grown on bare GaAs substrates. Journal of Crystal Growth, 1997, 182, 45-52.	1.5	5
148	Sub-bandgap optical absorption of MOVPE-GaN grown under controlled nucleation.. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1999, 59, 24-28.	3.5	5
149	TEM Study of the Behavior of Dislocations during ELO of GaN. Physica Status Solidi (B): Basic Research, 1999, 216, 691-695.	1.5	5
150	Microstructural analysis of IIIâ€“V nitrides grown on 6Hâ€“SiC by metalâ€“organic vapour phase epitaxy (MOVPE). Diamond and Related Materials, 2000, 9, 452-455.	3.9	5
151	High-Quality Distributed Bragg Reflectors for Resonant-Cavity Light-Emitting Diode Applications. Physica Status Solidi A, 2002, 192, 389-393.	1.7	5
152	Realization of waveguiding epitaxial GaN layers on Si by low-pressure metalorganic vapor phase epitaxy. Applied Physics Letters, 2003, 83, 5139-5141.	3.3	5
153	Mechanism of GaN quantum dot overgrowth by Al0.5Ga0.5N: Strain evolution and phase separation. Journal of Applied Physics, 2012, 111, 084309.	2.5	5
154	Silicon Growth on 3C-SiC(001)/Si(001): Pressure Influence and Thermal Effect. Materials Science Forum, 0, 821-823, 978-981.	0.3	5
155	Deep level traps in semiâ€polar nâ€GaN grown on patterned sapphire substrate by metalorganic vapor phase epitaxy. Physica Status Solidi (B): Basic Research, 2016, 253, 2225-2229.	1.5	5
156	Turning the undesired voids in silicon into a tool: In-situ fabrication of free-standing 3C-SiC membranes. Applied Physics Letters, 2017, 110, 081602.	3.3	5
157	Comparative Study Of Gan Movpe Growth Processes Using Two Different â€œSurface Preparation-Carrier Gasâ€• Combinations. Materials Research Society Symposia Proceedings, 1998, 512, 273.	0.1	4
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